



# **Phase Control Thyristor**

DS5894-5 January 2014 (LN31215)

## **FEATURES**

- Double Side Cooling
- High Surge Capability

## **APPLICATIONS**

- High Power Drives
- High Voltage Power Supplies
- Static Switches

## **VOLTAGE RATINGS**

Part and Ordering Number	Repetitive Peak Voltages V <sub>DRM</sub> and V <sub>RRM</sub> V	Conditions
DCR470G85* DCR470G80 DCR470G70	8500 8000 7000	$\begin{split} T_{vj} = -40^{\circ}\text{C to } 125^{\circ}\text{C}, \\ I_{DRM} = I_{RRM} = 100\text{mA}, \\ V_{DRM}, V_{RRM}  t_p = 10\text{ms}, \\ V_{DSM}  \&  V_{RSM} = \\ V_{DRM}  \&  V_{RRM} + 100V \\ respectively \end{split}$

Lower voltage grades available. \*8200V @ -40°C, 8500V @ 0°C

### ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

## DCR470G85

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

## **KEY PARAMETERS**

$V_{DRM}$	8500V
$I_{T(AV)}$	467A
I <sub>TSM</sub>	5250A
dV/dt*	1500V/µs
dl/dt	200A/us

# \* Higher dV/dt selections available

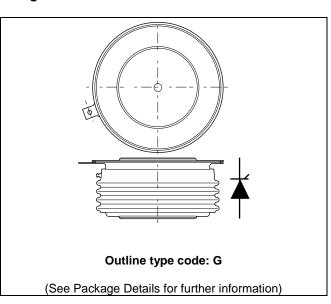


Fig. 1 Package outline



# **CURRENT RATINGS**

# $T_{\text{case}}$ = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Si	de Cooled			
I <sub>T(AV)</sub>	Mean on-state current	Half wave resistive load	467	Α
I <sub>T(RMS)</sub>	RMS value	-	734	Α
I <sub>T</sub>	Continuous (direct) on-state current	-	725	А

# **SURGE RATINGS**

Symbol	Parameter	Test Conditions	Max.	Units
I <sub>TSM</sub>	Surge (non-repetitive) on-state current	10ms half sine, $T_{case} = 125$ °C	5.25	kA
l <sup>2</sup> t	I <sup>2</sup> t for fusing	$V_R = 0$	0.138	MA <sup>2</sup> s

# THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
R <sub>th(j-c)</sub>	Thermal resistance – junction to case	Double side cooled	DC	-	0.0268	°C/W
		Single side cooled	Anode DC	-	0.0527	°C/W
			Cathode DC	-	0.0652	°C/W
R <sub>th(c-h)</sub>	Thermal resistance – case to heatsink	Clamping force 11.5kN Double side		-	0.0072	°C/W
		(with mounting compound)	Single side	-	.0144	°C/W
T <sub>vj</sub>	Virtual junction temperature	Blocking V <sub>DRM</sub> / <sub>VRRM</sub>		-	125	°C
T <sub>stg</sub>	Storage temperature range			-55	125	°C
F <sub>m</sub>	Clamping force			10	13	kN





# **DYNAMIC CHARACTERISTICS**

Symbol	Parameter	Test Conditio	ns	Min.	Max.	Units
I <sub>RRM</sub> /I <sub>DRM</sub>	Peak reverse and off-state current	At V <sub>RRM</sub> /V <sub>DRM</sub> , T <sub>case</sub> = 125°C		-	100	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% $V_{DRM}$ , $T_j = 125$ °C, ga	ate open	-	1500	V/µs
dl/dt	Rate of rise of on-state current	From 67% V <sub>DRM</sub> to 2x I <sub>T(AV)</sub>	Repetitive 50Hz	-	100	A/µs
		Gate source 30V, 10Ω,	Non-repetitive	-	200	A/µs
		$t_r < 0.5 \mu s, T_j = 125$ °C				
$V_{T(TO)}$	Threshold voltage – Low level	50A to 400A at T <sub>case</sub> = 125°C	;	-	1.162	V
	Threshold voltage – High level	400A to 1600A at T <sub>case</sub> = 125	5°C	-	1.3063	V
r <sub>T</sub>	On-state slope resistance – Low level	50A to 400A at T <sub>case</sub> = 125°C	;	-	3.153	mΩ
	On-state slope resistance – High level	400A to 1600A at T <sub>case</sub> = 125°C		-	2.763	mΩ
t <sub>gd</sub>	Delay time	$V_D = 67\% V_{DRM}$ , gate source 30V, $10\Omega$		-	3	μs
		$t_r = 0.5 \mu s, T_j = 25^{\circ}C$				
tq	Turn-off time	$T_j = 125$ °C, $V_R = 100$ V, $dI/dt = 5$ A/ $\mu$ s,		-	1200	μs
		dV <sub>DR</sub> /dt = 20V/μs linear				
Qs	Stored charge	$I_T = 500A$ , $T_j = 125$ °C, $dI/dt = 5A/\mu s$ ,		2000	3000	μC
IL	Latching current	$T_j = 25^{\circ}C, V_D = 5V$		-	3	А
I <sub>H</sub>	Holding current	$T_j = 25^{\circ}C, R_{G-K} = \infty, I_{TM} = 50^{\circ}$	0A, I <sub>T</sub> = 5A	-	300	mA



## **GATE TRIGGER CHARACTERISTICS AND RATINGS**

Symbol	Parameter	Test Conditions	Max.	Units
$V_{GT}$	Gate trigger voltage	$V_{DRM} = 5V$ , $T_{case} = 25$ °C	1.5	V
$V_{GD}$	Gate non-trigger voltage	At 50% V <sub>DRM</sub> , T <sub>case</sub> = 125°C	0.4	V
I <sub>GT</sub>	Gate trigger current	$V_{DRM} = 5V$ , $T_{case} = 25$ °C	350	mA
I <sub>GD</sub>	Gate non-trigger current	At 50% V <sub>DRM</sub> , T <sub>case</sub> = 125°C	10	mA

## **CURVES**

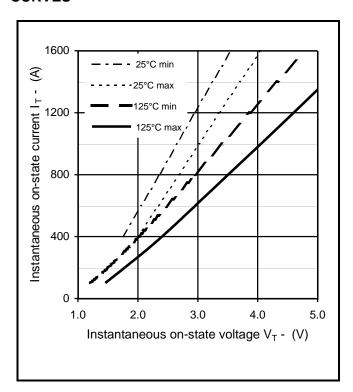
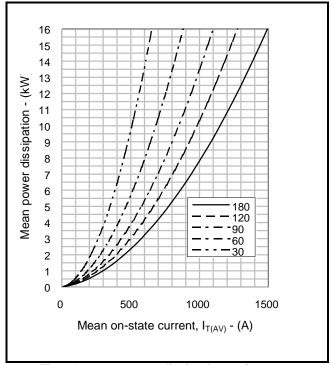
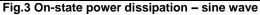


Fig.2 Maximum & minimum on-state characteristics

these values are valid for  $T_j$  = 125°C for  $I_T$  50A to 1600A







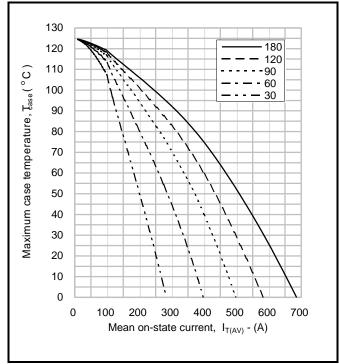


Fig.4 Maximum permissible case temperature, double side cooled – sine wave

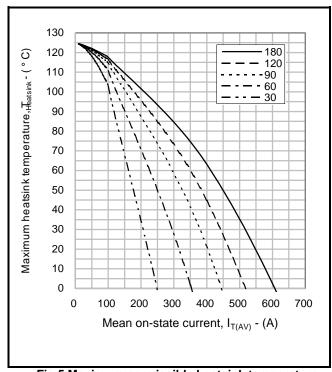


Fig.5 Maximum permissible heatsink temperature, double side cooled – sine wave

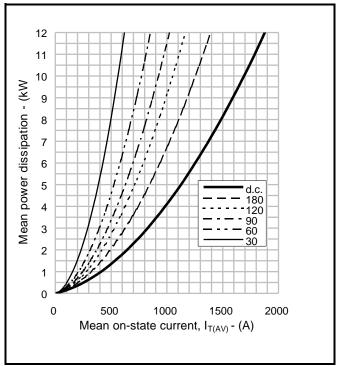
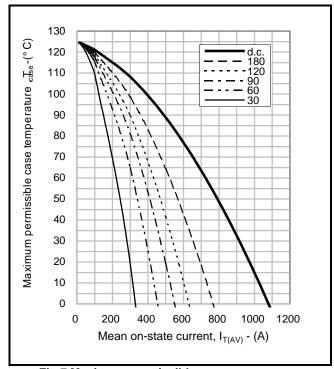
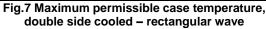


Fig.6 On-state power dissipation - rectangular wave







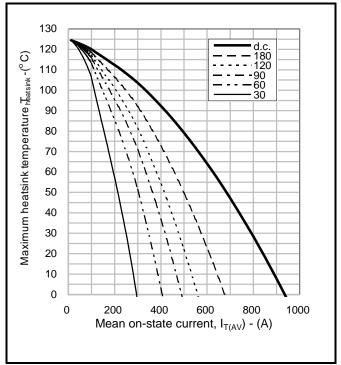
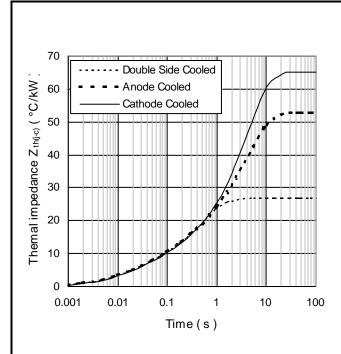


Fig.8 Maximum permissible heatsink temperature, double side cooled – rectangular wave



		1	2	3	4
Double side cooled	R <sub>i</sub> (°C/kW)	2.2995	5.4226	16.9074	2.1488
	T <sub>i</sub> (s)	0.0066401	0.0457025	0.4962482	1.8248
Anode side cooled	R <sub>i</sub> (°C/kW)	2.3214	5.2661	10.2686	34.8031
	T <sub>i</sub> (s)	0.0066948	0.045528	0.3484209	4.582
Cathode side cooled	R <sub>i</sub> (°C/kW)	2.4895	5.9105	7.4256	49.3432
	T; (s)	0.0070404	0.052895	0.3933903	4 2295

 $Z_{th} = \sum [R_i x (1-exp. (t/t_i))]$  [1]

 $\Delta R_{\text{th(j-c)}}$  Conduction

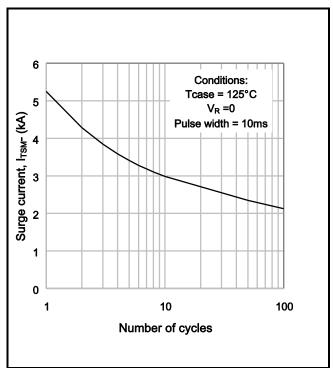
Tables show the increments of thermal resistance  $R_{\text{th}(j\text{-}c)}$  when the device operates at conduction angles other than d.c.

			_			
Double side cooling					Anode Side	Cooling
	$\Delta Z_{th}(z)$				$\Delta Z_t$	<sub>h</sub> (z)
θ°	sine.	rect.		θ°	sine.	rect.
180	4.15	2.72		180	4.15	2.72
120	4.90	4.02		120	4.89	4.02
90	5.74	4.79	ĺ	90	5.73	4.78
60	6.53	5.65		60	6.52	5.65
30	7.16	6.64		30	7.15	6.62

Ca	thode Sided Cooling				
	∆Z <sub>th</sub> (z)				
θ°	sine.	rect.			
180	4.13	2.71			
120	4.87	4.00			
90	5.69	4.76			
60	6.46	5.60			
30	7.07	6.56			
,	7 00	7.00			

Fig.9 Maximum (limit) transient thermal impedance – junction to case (°C/kW)







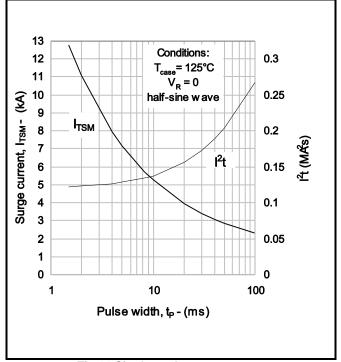


Fig.11 Single-cycle surge current

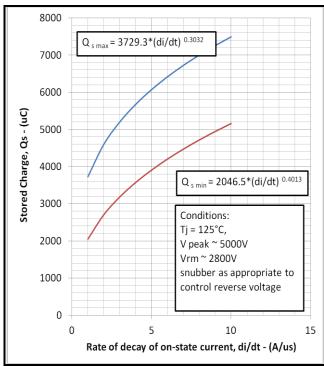


Fig.12 Stored charge

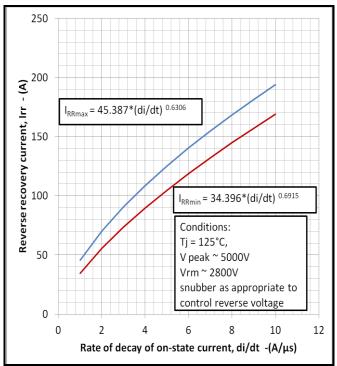


Fig.13 Reverse recovery current

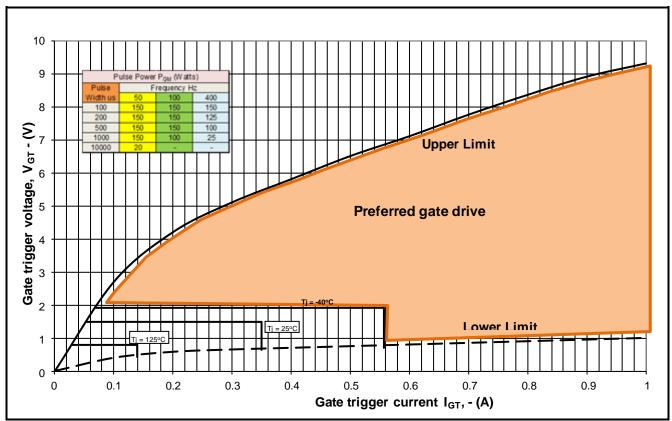


Fig14 Gate Characteristics

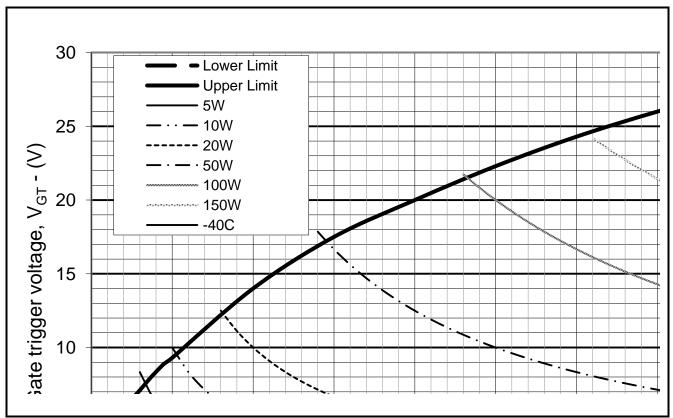


Fig. 15 Gate characteristics





### **PACKAGE DETAILS**

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.

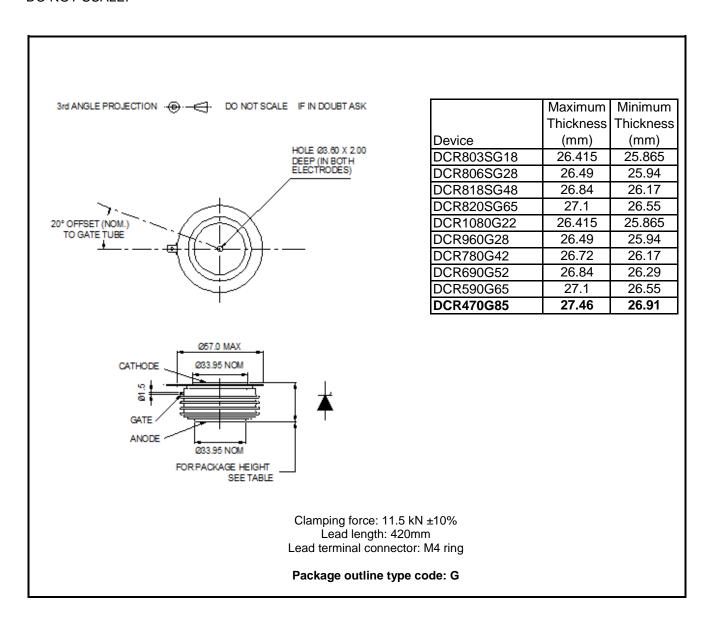


Fig.16 Package outline





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